# SUM70042E

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Vishay Siliconix



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	100				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = 10 V	0.0040				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_GS$ = 7.5 V	0.0045				
Q <sub>g</sub> typ. (nC)	84				
I <sub>D</sub> (A)	150 <sup>d</sup>				
Configuration	Single				

#### FEATURES

N-Channel 100 V (D-S) MOSFET

- TrenchFET<sup>®</sup> power MOSFET
- Maximum 175 °C junction temperature
- $\bullet$  Very low  $\mathsf{Q}_{gd}$  reduces power loss from passing through  $\mathsf{V}_{plateau}$
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **APPLICATIONS**

- Switching power supply
- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- Battery management
- OR-ing / e-fuse

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N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and halogen-free	SUM70042E-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \degree C$ , unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	100	V	
Gate-source voltage		V <sub>GS</sub>	± 20	v	
Continuous drain current ( $T_J = 150 \ ^{\circ}C$ )	T <sub>C</sub> = 25 °C		150 <sup>d</sup>		
	T <sub>C</sub> = 70 °C		139	A	
Pulsed drain current (t = 100 µs)		I <sub>DM</sub>	200	A	
Avalanche current		I <sub>AS</sub>	50		
Single avalanche energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	125	mJ	
Ma 'a a a a a d'a 'a d'a d'a d	T <sub>C</sub> = 25 °C	D-	278 <sup>b</sup>	w	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 125 °C	P <sub>D</sub>	178 <sup>b</sup>	vv	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient (PCB mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W	
Junction-to-case (drain)	R <sub>thJC</sub>	0.55	0/11	

#### Notes

a. Duty cycle ≤ 1 %

b. See SOA curve for voltage derating

c. When mounted on 1" square PCB (FR4 material)

d. Package limited

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HALOGEN

FREE

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	•						
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_{D} = 10 mA$	100	-	-		
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2	-	4	V	
Gate-body leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	-	-	± 250	nA	
		$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1		
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	150	μA	
-		$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	5	mA	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	50	-	-	А	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	0.0033	0.0040	Ω	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 15 A	-	0.0036	0.0045		
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	-	60	-	S	
Dynamic <sup>b</sup>	1						
Input capacitance	C <sub>iss</sub>		-	6490	-	pF	
Output capacitance	C <sub>oss</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 50 V, f = 1 MHz	-	570	-		
Reverse transfer capacitance	C <sub>rss</sub>		-	20	-		
Total gate charge <sup>c</sup>	Qg		-	84	110		
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	33.5	-	nC	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>		-	9.5	-		
Gate resistance	Rg	f = 1 MHz	0.26	1.3	2.6	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>		-	25	50		
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, \text{ R}_{\text{I}} = 5 \Omega$	-	18	36		
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{\text{GEN}} = 10 \text{ V}, R_g = 1 \Omega$	-	45	90	ns	
Fall time <sup>c</sup>	t <sub>f</sub>		-	14	28		
Drain-Source Body Diode Ratings	and Characte	ristics <sup>b</sup> (T <sub>C</sub> = 25 °C)					
Pulsed current (t = 100 µs)	I <sub>SM</sub>		-	-	200	А	
Forward voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.8	1.5	V	
Reverse recovery time	t <sub>rr</sub>		-	58	116	ns	
Peak reverse recovery charge	I <sub>RM(REC)</sub>		-	3.9	5.9	А	
Reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs	-	126	189	μC	
Reverse recovery fall time	ta		-	42	-		
Reverse recovery rise time	t <sub>b</sub>		-	16	-	ns	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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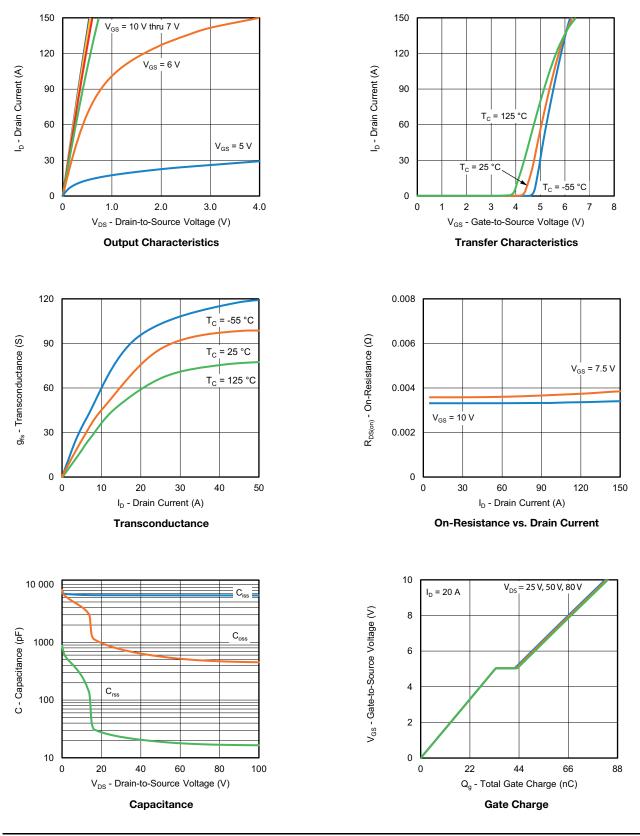
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# SUM70042E

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### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



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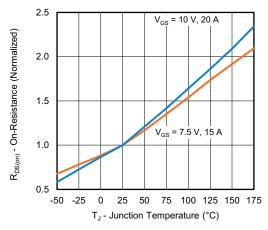
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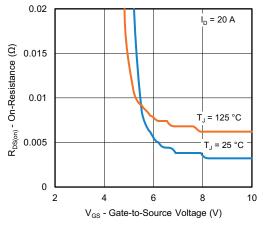
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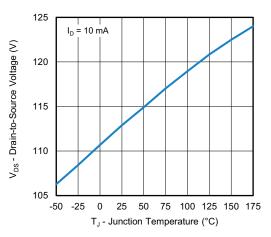
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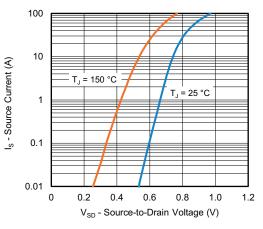
**On-Resistance vs. Junction Temperature** 



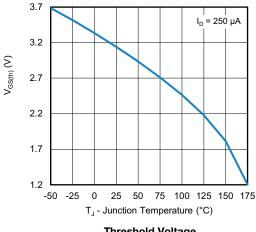
**On-Resistance vs. Gate-to-Source Voltage** 



**Drain Source Breakdown vs. Junction Temperature** 



Source Drain Diode Forward Voltage



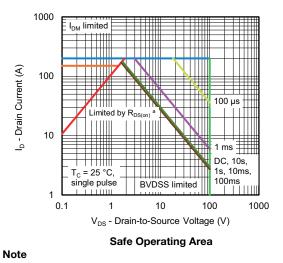
Threshold Voltage

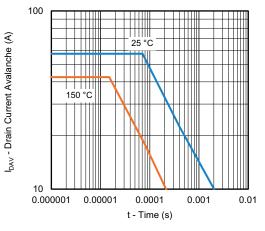
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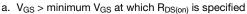
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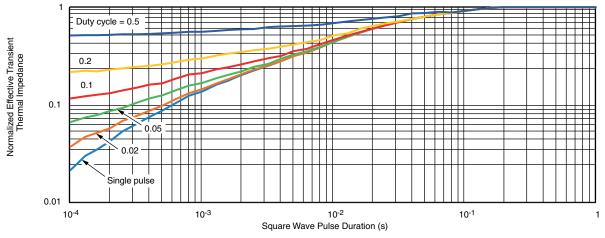
### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)





Single Pulse Avalanche Current Capability vs. Time





Normalized Thermal Transient Impedance, Junction-to-Case

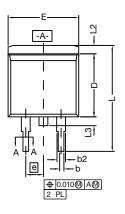
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TO-263 (D<sup>2</sup>PAK): 3-LEAD









DETAIL A (ROTATED 90°)



		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
A		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
E2		0.355	0.375	9.017	9.525	
E3		0.072	0.078	1.829	1.981	
	е	0.100 BSC		2.54 BSC		
	К	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4 0.010 BSC		0.254 BSC			
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843						

#### Notes

- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25 % of L1 can fall above seating plane by
- max. 8 mils. 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB.
  - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

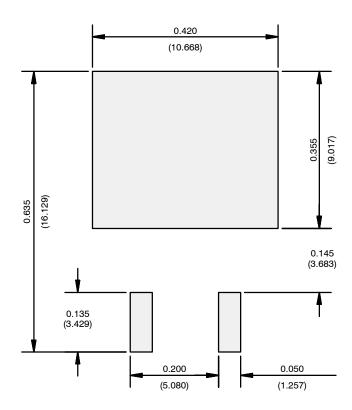
6. This feature is for thick lead.

Revison: 30-Sep-13

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### **RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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